i-nolar transistors

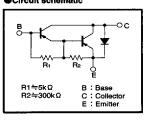
Power Transistor (-100V, -8A)

2SB1344

●Features

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SD2025.

Circuit schematic



●Absolute maximum ratings (Ta=25℃)

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	100	V
Collector-emitter voltage	VCEO	-100	V
Emitter-base voltage	VEBO	-7	٧
Collector current		-8	A (DC)
	lc lc	-10	A (Pulse)
Power dissipation		2	w
	Pc	30	W (Tc=25℃)
Junction temperature	Tj	150	ኄ
Storage temperature	Tstg	-55~150	°C

^{*} Single pulse Pw=100ms

●Packaging specifications and hre

Туре	2SB1344	
Package	TO-220FP	
hre	1k~20k	
Code	_	
Basic ordering unit (pieces)	500	

●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	-100	_	_	٧	Ic=-50 μ A	
Collector-emitter breakdown voltage	BVceo	-100	-	_	٧	Ic=-5mA	
Collector cutoff current	Ісво	-		-10	μΑ	Vce=-100V	
Emitter cutoff current	І ЕВО		_	-3	mA	V _{E8} =-5V	
Collector-emitter saturation voltage	VCE(sat)	_	1.0	-1.5	V	lc/ls=-3A/-6mA	*1
DC current transfer ratio	hre	1000	10000	20000		Vce/lc=-3V/-2A	*1
Transition frequency	fr	— ·	12		MHz	Vce=-5V, le=0.5A, f=10MHz	*2
Output capacitance	Cob	_	90	_	рF	Vcs=-10V, IE=0A, f=1MHz	

*1 Measured using pulse current.

*2 Transition frequency of mounted transistor.

(94L-374-B403)

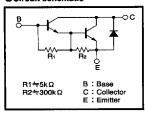
Power Transistor (100V, 8A)

2SD2025

Features

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SB1344.

Circuit schematic



●Absolute maximum ratings (Ta=25℃)

Parameter	Symbol	Limits	Unit
Collector-base voltage	Voso	100	V
Collector-emitter voltage	VCEO	100	V
Emitter-base voltage	VEBO	7	V
Collector current	lc ·	8	A (DC)
		10	A (Pulse) *
Power dissipation		2	W
	Pc	30	W (Tc=25℃)
Junction temperature	Tj	150	ొ
Storage temperature	Tstg	-55~150	2

* Sigle pulse Pw=10ms

●Packaging specifications and hre

Туре	2SD2025
Package	TO-220FP
hee	1k~20k
Code	
Basic ordering unit (pleces)	500

●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	100	_	-	V	lc=50 μA	
Collector-emitter breakdown voltage	BVCED	100	_	_	V	lc=5mA	
Collector cutoff current	Ісво			10	μΑ	Vc8=100V	
Emitter cutoff current	lebo		_	3	mA	VEB=5V	
Collector-emitter saturation voltage	VCE(eat)	_	_	1.5	V	Ic/Is=3A/6mA	*1
DC current transfer ratio	hre	1000	_	20000	_	Vce/lc=3V/2A	*1
Transition frequency	fτ	_	40	T -	MHz	Vc==5V , Ie=-0.2A , f=10MHz	*2
Output capacitance	Cob		50	T —	рF	Vcs=10V, IE=0A, f=1MHz	-

*1 Measured using pulse current.

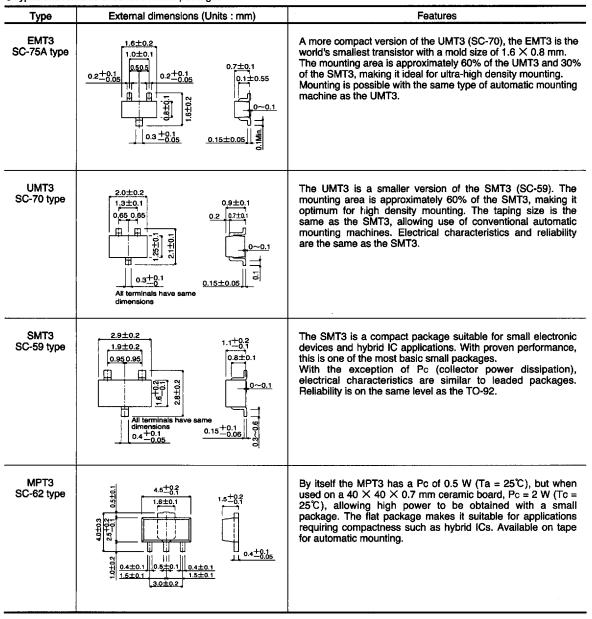
*2 Transition frequency of mounted transistor.

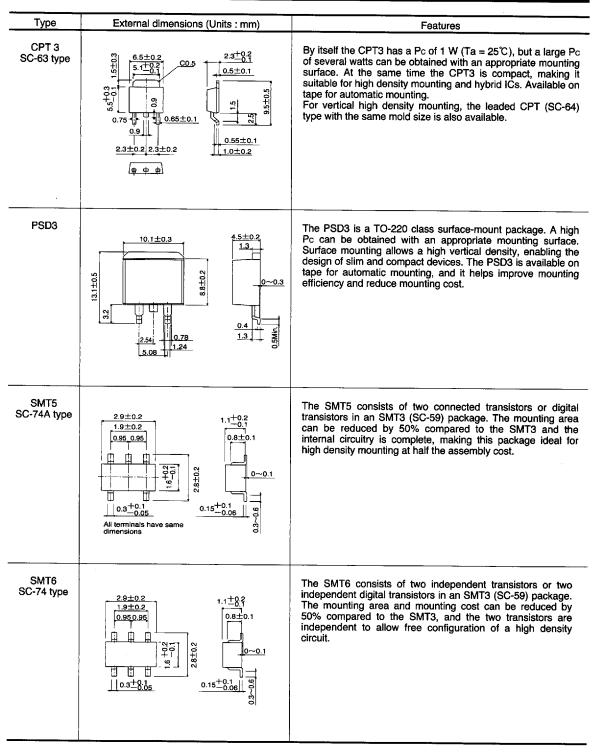
(94L-969-D403)

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

●Types and features of surface-mount packages

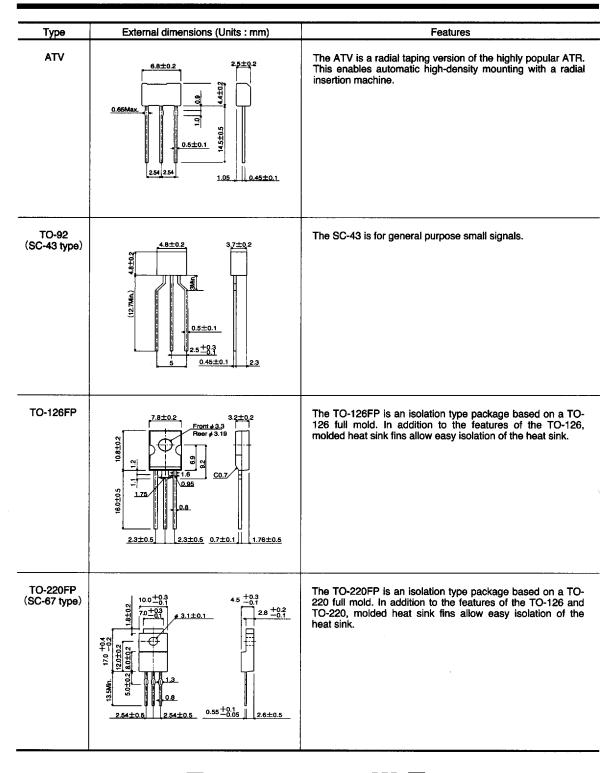




Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,85 0,85 0,7 0,005 All terminals have same dimensions	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1,3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

●Types and features of leaded packages

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.4±0.2 0.55±0.1 0.55±0.1 0.45±0.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 2.4±0.2 0.65Max 2.4±0.2 0.5±0.1 0.5±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max	SC-71type with a height of 4.4 mm and a Pc=1W type.



Туре	External dimensions (Units : mm)	Features
TO-220FN	10.0 ±0.3 4.5 ±0.3 4.5 ±0.3 4.5 ±0.3 2.8 ±0.2 2.8 ±	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.